

Customer No.: 31561  
Application No.: 10/710,422  
Docket No.: 11572-US-PA

### AMENDMENTS

#### In the Claims:

Please amend the claims according to the following listing of claims and substitute it for all prior versions and listing of claims in the application.

1. (currently amended) An under bump metallurgic (UBM) layer adapted for a chip, the chip comprising a bonding pad and a transmission line coupled thereto, wherein the UBM layer is formed over the bonding pad and the UBM layer comprises a plurality of metal layers and at least one liner layer, and the liner layer is formed among the metal layers, wherein the liner layer is formed only close to an end of the transmission line which is connected to the bonding pad for a portion of the UBM layer which is close to the transmission line is be thicker than a portion of the UBM layer which is away from the transmission line.

2. (cancelled)

3. (currently amended) The UBM layer of claim 1, wherein the liner layer comprises a material the same as a material of at least one of the metal layers.

4. (original) The UBM layer of claim 1, wherein a material of the UBM layer is selected from the group consisting of Al, Ti, W, Cr, Ni, Cu, Au, and an alloy thereof.

5. (cancelled)

Customer No.: 31561  
Application No.: 10/710,422  
Docket No.: 11572-US-PA

6. (currently amended) A conductive structure over a bonding pad, adapted for a chip, the chip comprising ~~a~~ the bonding pad and a transmission line coupled thereto, the conductive structure comprising:

an under bump metallurgical (UBM) layer formed over the bonding pad, wherein the UBM layer comprises a plurality of metal layers, and only a portion of one of the metal layers at a region which is close to the transmission line is thicker than a remaining portion of the one of the metal layers which is away from the transmission line for a portion of the UBM layer which is close to the transmission line ~~is~~ be thicker than a portion of the UBM layer which is away from the transmission line; and

a conductive bump, wherein a bottom of the conductive bump is connected to the UBM layer.

7-8. (cancelled)

9. (original) The conductive structure of claim 6, wherein a material of the UBM layer is selected from the group consisting of Al, Ti, W, Cr, Ni, Cu, Au, and an alloy thereof.

10. (cancelled)

11. (original) The conductive structure of claim 6, wherein the conductive bump comprises a Sn-Pb alloy.

Customer No.: 31561  
Application No.: 10/710,422  
Docket No.: 11572-US-PA

12. (new) An under bump metallurgic (UBM) layer adapted for a chip, the chip comprising a bonding pad and a transmission line coupled thereto, wherein the UBM layer is formed over the bonding pad and the UBM layer comprises a plurality of metal layers, and only a portion of one of the metal layers at a region which is close to the transmission line is thicker than a remaining portion of the one of the metal layers which is away from the transmission line such that a portion of the UBM layer which is close to the transmission line is thicker than a portion of the UBM layer which is away from the transmission line.

13. (new) The UBM layer of claim 12, wherein a material of the UBM layer is selected from the group consisting of Al, Ti, W, Cr, Ni, Cu, Au, and an alloy thereof.